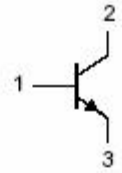
isc Silicon NPN Power Transistor — 2N6739

DESCRIPTION

- Collector-Emitter Sustaining Voltage-
  : $V_{CEO(SUS)}$ = 350V(Min)
- High Switching Speed
- Low Saturation Voltage
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



PIN 1. BASE
2.COLLECTOR
3. EMITTER
TO-220C package

APPLICATIONS

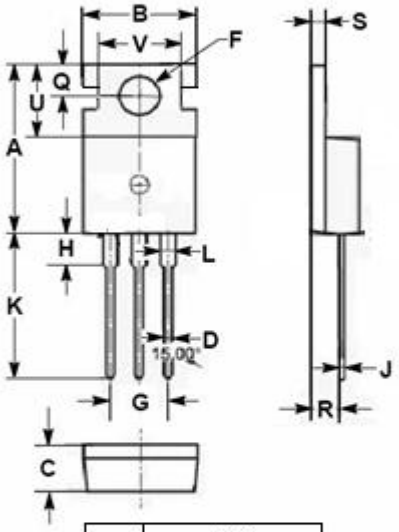
- Designed for use in high-voltage, high-speed , power switching in inductive circuit , they are particularly suited for 115 and 220V switchmode applications such as switching regulators, inverters, DC-DC and converter.

ABSOLUTE MAXIMUM RATINGS(T_a=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CEV}	Collector-Emitter Voltage-V_{BE}= -1.5V	550	V
V_{CEX}	Collector-Emitter Voltage-V_{BE}= -1.5V	400	V
V_{CEO}	Collector-Emitter Voltage	350	V
V_{EBO}	Emitter-Base Voltage	8	V
I_C	Collector Current-Continuous	8	A
I_{CM}	Collector Current-Peak	10	A
I_B	Base Current-Continuous	4	A
P_C	Collector Power Dissipation T_C=25℃	100	W
T_j	Junction Temperature	150	℃
T_{stg}	Storage Ttemperature Range	-65~150	℃

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j\text{-}c}$	Thermal Resistance,Junction to Case	1.25	℃/W



DIM	mm MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	I_C= 50mA; I_B= 0	350		V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	I_C= 5A; I_B= 1A		1	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	I_C= 8A; I_B= 4A		2	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	I_C= 5A; I_B= 1A		1.6	V
I_{EBO}	Emitter Cutoff Current	V_{EB}= 8V; I_C= 0		2	mA
h_{FE}	DC Current Gain	I_C= 5A ; V_{CE}= 3V	10	40	
f_T	Current-Gain—Bandwidth Product	I_C= 0.2A; V_{CE}= 10V, f_{test}= 1MHz	10		MHz
Switching Times; Resistive Load					
t_d	Delay Time	I_C= 5A; I_{B1}= -I_{B2}= 1A,V_{CC}= 125V; t_p= 20μs, Duty Cycle≤1%		0.1	μs
t_r	Rise Time			0.4	μs
t_s	Storage Time			2.5	μs
t_f	Fall Time			0.5	μs